PMV185XN

30 V, single N-channel Trench MOSFET

3 August 2012 Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low R_{DSon}
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

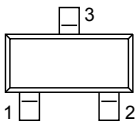
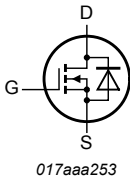
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_{amb} = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	1.2	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 1.1 A; T_j = 25 °C		-	185	250	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-236AB (SOT23)	 017aaa253
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV185XN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV185XN	EH%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_{amb} = 25 °C		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	1.2	A
		V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	1.1	A
		V_{GS} = 4.5 V; T_{amb} = 100 °C	[1]	-	0.7	A
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; t_p ≤ 10 µs		-	4.4	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	325	mW
			[1]	-	455	mW
		T_{sp} = 25 °C		-	1275	mW

Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	0.7	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	333	385	K/W
			[2]	-	240	275	K/W
		in free air; t ≤ 5 s	[2]	-	203	235	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	85	100	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 1.1 A; T_j = 25 °C		-	185	250	mΩ
		V_{GS} = 4.5 V; I_D = 1.1 A; T_j = 150 °C		-	300	400	mΩ
		V_{GS} = 2.5 V; I_D = 0.25 A; T_j = 25 °C		-	255	365	mΩ
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 1.1 A; T_j = 25 °C		-	2.9	-	S
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = 15 V; I_D = 1.1 A; V_{GS} = 4.5 V; T_j = 25 °C		-	0.87	1.3	nC
Q_{GS}	gate-source charge			-	0.17	-	nC
Q_{GD}	gate-drain charge			-	0.24	-	nC
C_{iss}	input capacitance	V_{DS} = 15 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	76	-	pF
C_{oss}	output capacitance			-	30	-	pF
C_{rss}	reverse transfer capacitance			-	22	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; I_D = 1.1 A; V_{GS} = 4.5 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	7	-	ns
t_r	rise time			-	11	-	ns
$t_{d(off)}$	turn-off delay time			-	16	-	ns
t_f	fall time			-	7	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 0.7 A; V_{GS} = 0 V; T_j = 25 °C		-	0.8	1.2	V